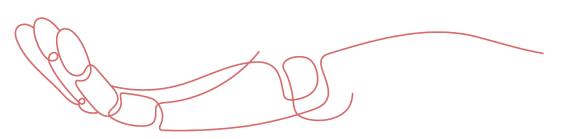


## **PRODUCT DATA SHEET**



To learn more about JGSEMI, please visit our website at







Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to Fairchild\_questions@jgsemi.com.



#### **Features**

- 60Watts peak pulse power (tp = 8/20µs)
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance (Cj=0.2pF typ. I/O to I/O)
- IEC 61000-4-2 ±20kV contact ±25kV air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 4A (8/20μs)



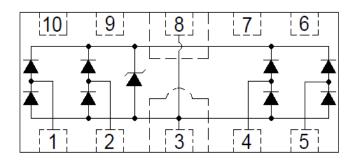
## **Applications**

- USB3.0, USB2.0, Ethernet
- HDMI 2.0, Displayport 1.3,eSATA
- Unified Display interface
- Digital Visual Interface
- High speed serial interface

#### **Mechanical Data**

- Tiny DFN2510(2.5mmx1.0mm) package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

### **Schematic & PIN Configuration**





**Absolute Maximum Rating** 

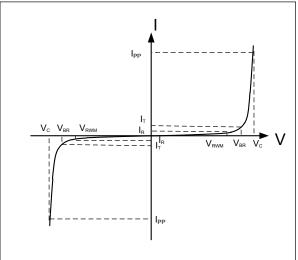
Rating	Symbol	Value	Units	
Peak Pulse Power ( t <sub>p</sub> =8/20μs )	P <sub>PP</sub>	60	Watts	
Peak Pulse Current ( t <sub>p</sub> =8/20μs ) (note1)	I <sub>PP</sub>	4	А	
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V <sub>ESD</sub>	25 20	kV	
Lead Soldering Temperature	T <sub>L</sub>	260(10seconds)	${\mathbb C}$	
Junction Temperature	TJ	-55 to + 125	${}^{\mathbb{C}}$	
Storage Temperature	T <sub>stg</sub>	-55 to + 125	$^{\circ}$ C	

### **Electrical Characteristics**

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	$V_{RWM}$				5.0	V
Reverse Breakdown Voltage	$V_{BR}$	I <sub>T</sub> =1mA	6.0			V
Reverse Leakage Current	I <sub>R</sub>	V <sub>RWM</sub> =5V,T=25℃			1	μΑ
Peak Pulse Current	I <sub>PP</sub>	tp =8/20μs			4	Α
Clamping Voltage	V <sub>C</sub>	I <sub>PP</sub> =4A,t <sub>p</sub> =8/20μs			15	V
Junction Capacitance	C <sub>j</sub>	V <sub>R</sub> = 0V, f = 1MHz I/O to I/O		0.2	0.3	, F
		V <sub>R</sub> = 0V, f = 1MHz I/O to GND		0.4	0.55	pF

## **Electrical Parameters (TA = 25°C unless otherwise noted)**

	Parameter
<b>I</b> PP	MaximumReversePeak Pulse Current
Vc	Clamping Voltage @ IPP
VRWM	WorkingPeak Reverse Voltage
lR	Maximum Reverse Leakage Current @ VRWM
V <sub>BR</sub>	Breakdown Voltage @ I⊤
lτ	Test Current



Note: 8/20µs pulse waveform.



### **Typical Characteristic Curves**

Fig.1 Peak Pulse Power Rating Curve

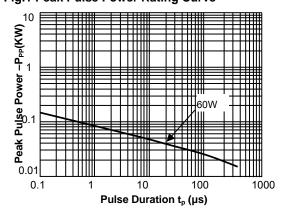


Fig.3 Pulse Waveform-8/20µs

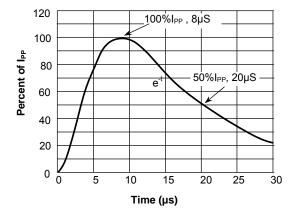


Fig.2 Pulse Derating Curve

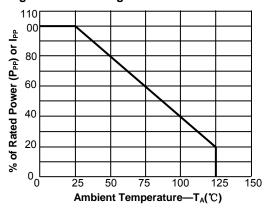
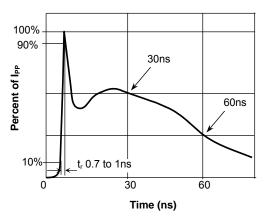
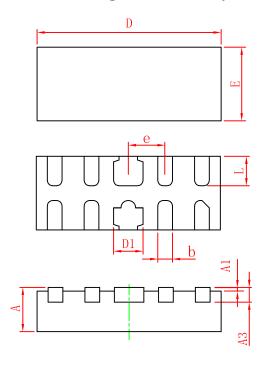


Fig.4 Pulse Waveform-ESD(IEC61000-4-2)





# Outline Drawing – DFN2510(2.5mmx1.0mm)



Symbol	Dimensions in millimeters				
	Min	Nom	Max		
Α	0.45	0.50	0.55		
A1	-	0.02	0.05		
A3	0.10	0.15	0.20		
D	2.45	2.50	2.55		
E	0.95	1.00	1.05		
D1	0.35	0.40	0.45		
b	0.15	0.20	0.25		
е	0.50BSC				
L	0.35	0.40	0.45		



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